PDTD123T series

NPN 500 mA, 50 V resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

Rev. 03 — 16 November 2009

Product data sheet

1. Product profile

1.1 General description

500 mA NPN Resistor-Equipped Transistors (RET) family.

Table 1. Product overview

Type number	Package			PNP complement		
	NXP	JEITA	JEDEC			
PDTD123TK	SOT346	SC-59A	TO-236	PDTB123TK		
PDTD123TS[1]	SOT54	SC-43A	TO-92	PDTB123TS		
PDTD123TT	SOT23	-	TO-236AB	PDTB123TT		

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2).

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- 500 mA output current capability
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Digital application in automotive and industrial segments
- Controlling IC inputs

- Cost saving alternative for BC817 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	500	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ



2. Pinning information

3

output (collector)

Table 3. **Pinning** Simplified outline Pin **Description Symbol** SOT54 1 input (base) 2 output (collector) 3 GND (emitter) R1 001aab347 SOT54A 1 input (base) 2 output (collector) 3 GND (emitter) R1 001aab348 006aaa218 **SOT54** variant 1 input (base) 2 output (collector) 3 GND (emitter) R1 001aab447 006aaa218 **SOT23, SOT346** 1 input (base) 3 2 GND (emitter)

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sym012

006aaa144

3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PDTD123TK	SC-59A	plastic surface mounted package; 3 leads	SOT346			
PDTD123TS[1]	SC-43A	plastic single-ended leaded (through hole) package; 3 leads	SOT54			
PDTD123TT	-	plastic surface mounted package; 3 leads	SOT23			

^[1] Also available in SOT54A and SOT54 variant packages (see Section 2 and Section 9).

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTD123TK	E9
PDTD123TS	TD123TS
PDTD123TT	*1T

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	50	V
V _{CEO}	collector-emitter voltage	open base	-	50	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
VI	input voltage				
	positive		-	+12	V
	negative		-	- 5	V
Io	output current		-	500	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1]		
	SOT346		-	250	mW
	SOT54		-	500	mW
	SOT23		-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]			
	SOT346		-	-	500	K/W
	SOT54		-	-	250	K/W
	SOT23		-	-	500	K/W

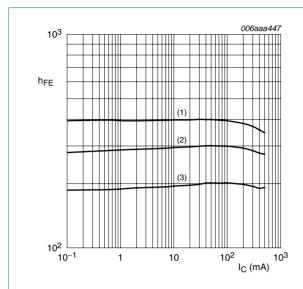
^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

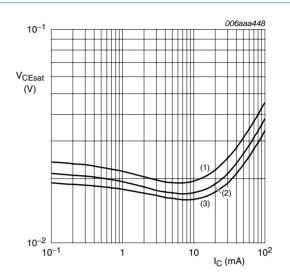
 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO} collector-bas current	collector-base cut-off	$V_{CB} = 40 \text{ V}; I_{E} = 0 \text{ A}$	-	-	100	nA
	current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = 50 \text{ V}; I_{B} = 0 \text{ A}$	-	-	0.5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 50 \text{ mA}$	100	300	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}$	-	-	0.3	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	7	-	pF



- $V_{CE} = 5 V$
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

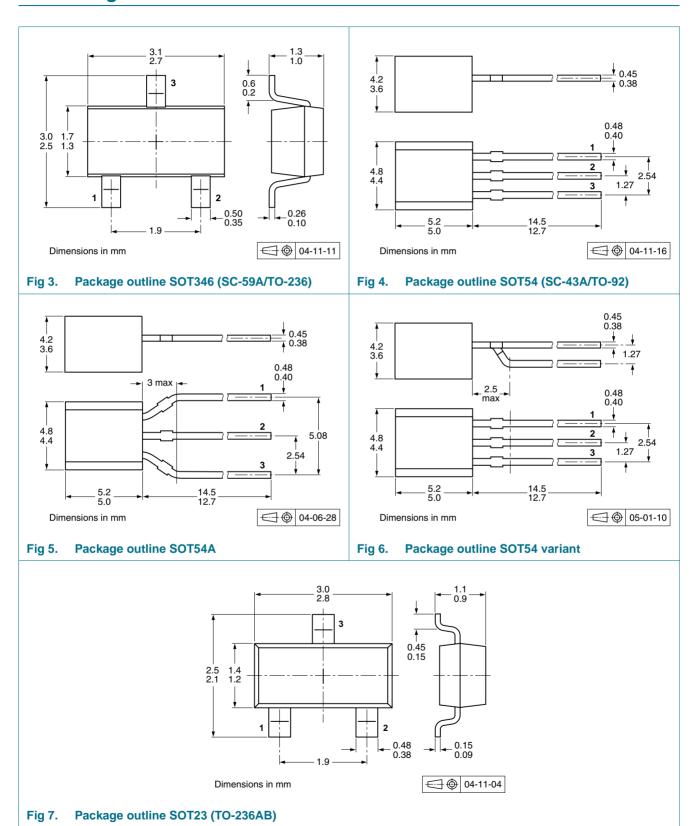
Fig 1. DC current gain as a function of collector current; typical values



- $I_{\rm C}/I_{\rm B} = 20$
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -40 \, ^{\circ}C$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values

8. Package outline



Product data sheet

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NPN 500 mA resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

Packing information 9.

Table 9. **Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity			
			3000	5000	10000	
PDTD123TK	SOT346	4 mm pitch, 8 mm tape and reel	-115	-	-135	
PDTD123TS	SOT54	bulk, straight leads	-	-412	-	
	SOT54A	tape and reel, wide pitch	-	-	-116	
		tape ammopack, wide pitch	-	-	-126	
	SOT54 variant	bulk, delta pinning	-	-112	-	
PDTD123TT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235	

^[1] For further information and the availability of packing methods, see Section 12.



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NPN 500 mA resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

10. Revision history

Table 10. Revision history

Product data sheet

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Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTD123T_SER_3	20091116	Product data sheet	-	PDTD123T_SER_2
Modifications:		eet was changed to reflect w legal definitions and disc		
PDTD123T_SER_2	20050721	Product data sheet	-	PDTD123T_SER_1
PDTD123T_SER_1	20050603	Product data sheet	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTD123T_SER_3

PDTD123T series

NPN 500 mA resistor-equipped transistors; R1 = 2.2 k Ω , R2 = open

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Date of release: 16 November 2009 Document identifier: PDTD123T_SER_3

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